## N-Channel 30-V (D-S) MOSFET

### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

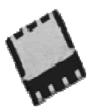
### **Typical Applications:**

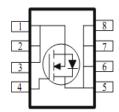
- DC/DC Conversion
- Power Routing
- Motor Drives

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	I□ (A)				
30	4.6 @ V <sub>GS</sub> = 10V	27			
	$5.5 @ V_{GS} = 4.5V$	25			









ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter				Limit	Units		
Drain-Source Voltage				30	V		
Gate-Source Voltage				±20	V		
Continuous Drain Comment <sup>a</sup>		T <sub>A</sub> =25°C		27			
Continuous Drain Current <sup>a</sup>		T <sub>A</sub> =70°C	I <sub>D</sub>	22	Α		
Pulsed Drain Current <sup>b</sup>				100	'		
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	6.7	Α				
Device Discipation a		T <sub>A</sub> =25°C	P <sub>D</sub>	5	W		
Power Dissipation <sup>a</sup>		T <sub>A</sub> =70°C	' D	3.2	VV		
Operating Junction and Storage Temperature Range				-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
IMAXIIIIUIII JUIICIIOII-IO-AIIIDIEIII	Steady State		65	C/VV			

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

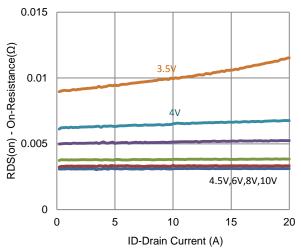
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Brain Gurrent	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	10		u/\		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
	r	$V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$			4.6	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$			5.5	11122	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		12		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 3.4 \text{ A}, V_{GS} = 0 \text{ V}$		0.76		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		35			
Gate-Source Charge	$Q_gs$	$I_{D} = 20 \text{ A}$		13		nC	
Gate-Drain Charge	$Q_gd$	10 = 20 / (		13			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 15 \text{ V}, R_1 = 0.8 \Omega,$		11			
Rise Time	t <sub>r</sub>	$I_{DS} = 13 \text{ V}, N_{L} = 0.0 \Omega_{2},$ $I_{D} = 20 \text{ A},$		16		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		76			
Fall Time	t <sub>f</sub>	VGEN = 10 V; NGEN 0 12		27			
Input Capacitance	$C_{iss}$			3876		_	
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		410		pF	
Reverse Transfer Capacitance	$C_{rss}$			339			

#### Notes

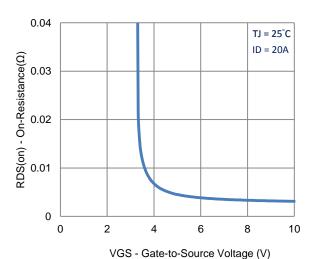
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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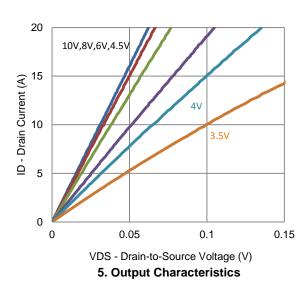
### **Typical Electrical Characteristics**

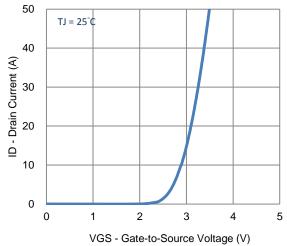


#### 1. On-Resistance vs. Drain Current

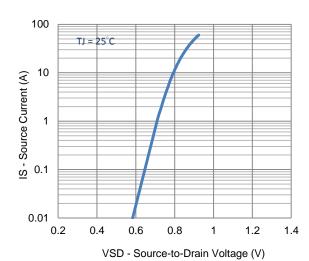


3. On-Resistance vs. Gate-to-Source Voltage

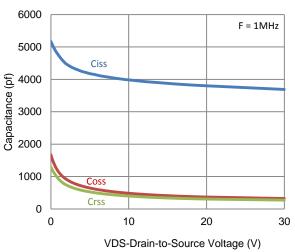




2. Transfer Characteristics

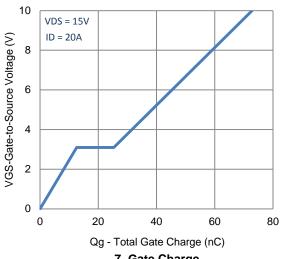


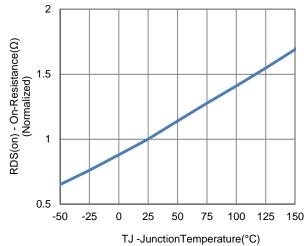
4. Drain-to-Source Forward Voltage



6. Capacitance

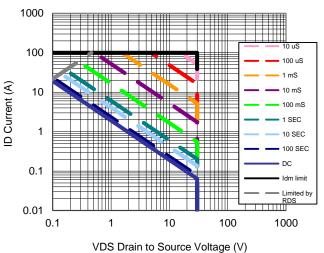
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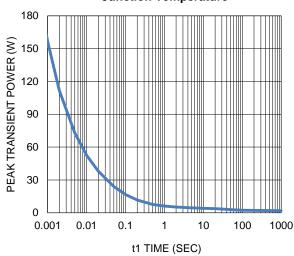




7. Gate Charge

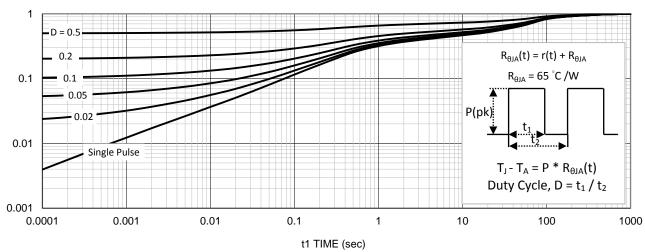






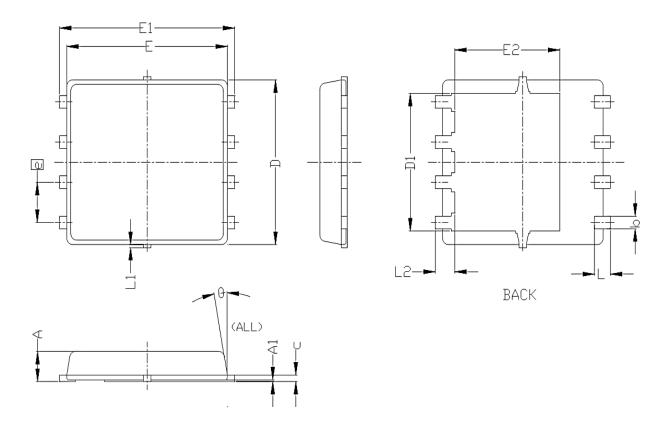
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# Package Information



CAN ADOL C	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SYMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е		5, 55 BSC 0, 219 BSC					
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	